Abstracts

K-Band Power GaAs FETs

L.S. Rosenheck, D. Herstein and I. Drukier. "K-Band Power GaAs FETs." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 28-30.

This paper will report on the structure and performance of GaAs FETs developed for K-band applications. A power output of 27dBm was obtained with 5dB gain at 21GHz. A novel low loss waveguide to microstrip transition was used in the measurement. Its design will be described.

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